

## UNISONIC TECHNOLOGIES CO., LTD

UT12N10 Preliminary Power MOSFET

# 12 Amps, 100 Volts N-CHANNEL POWER MOSFET

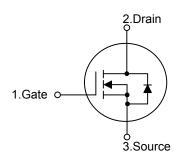
## ■ DESCRIPTION

The UTC **UT12N10** is an N-channel mode Power FET using UTC's advanced technology to provide custumers with minimum on-state resistance by extremely high dense cell design. Moreover, it's good at handing high power and current.

#### **■ FEATURES**

- \* 100V, 12A,  $R_{DS(ON)} = 180 \text{m}\Omega$  @ $V_{GS} = 10V$ .
- \* Be good at handing high power and current.
- \* Very high dense cell design for super low R<sub>DS(ON)</sub>.
- \* Lead free product is acquired.

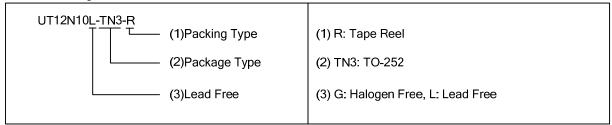


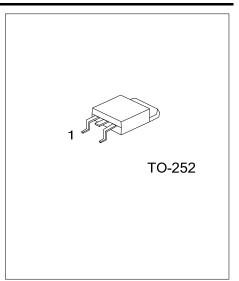


#### **■ ORDERING INFORMATION**

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UT12N10L-TN3-R	UT12N10G-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source





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## ■ ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub>=25°C, unless otherwise noted)

PARAM	PARAMETER SYMBOL RATINGS		UNIT	
Drain-Source Voltage		$V_{DSS}$	100	V
Gate-Source Voltage		$V_{GSS}$	V <sub>GSS</sub> ±20	
Dania Orana at	Continuous	I <sub>D</sub>	12	Α
Drain Current	Current Pulsed (Note 1) I <sub>DM</sub> 44	Α		
Power Dissipation		P <sub>D</sub>	43	W/°C
Junction Temperature		$T_J$	+150	°C
Storage Temperature		T <sub>STG</sub>	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Note:1 Repetitive Rating: Pulse width limited by maximum junction temperature

#### **■ THERMAL CHARACTERISTICS**

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient (Note 2)	$ heta_{JA}$	50	°C/W	
Junction to Case	$\theta_{JC}$	3.5	°C/W	

Note:  $\theta_{JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.

 $\theta_{\text{JC}}$  is guaranteed by design while  $\theta_{\text{JA}}$  is determined by the user's board design.

Note: 2 When mounted on a 1 in 2 pad of 2 oz copper

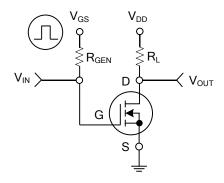
## ■ **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub>=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V				V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μΑ
Gate- Source Leakage Current Forward	]	V <sub>GS</sub> =+20V, V <sub>DS</sub> =0V			+100	nA
Reverse	$I_{GSS}$	V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V			-100	nA
ON CHARACTERISTICS (Note 1)						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu A$			4	V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =6A		150	180	mΩ
Forward Transconductance	<b>g</b> fs	$V_{DS}$ =10V, $I_{D}$ =6A		5		S
DYNAMIC PARAMETERS (Note 2)						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz		430		pF
Output Capacitance	Coss			90		pF
Reverse Transfer Capacitance	$C_{RSS}$			20		pF
SWITCHING PARAMETERS (Note 2)						
Total Gate Charge	$Q_G$	V <sub>GS</sub> =10V, V <sub>DS</sub> =80V, I <sub>D</sub> =12A		8	16	nC
Gate to Source Charge	$Q_GS$			1.5		nC
Gate to Drain Charge	$Q_GD$			2		nC
Turn-ON Delay Time	t <sub>D(ON)</sub>			12	24	ns
Rise Time	t <sub>R</sub>	$V_{DD}$ =80V, $I_{D}$ =12A, $V_{GS}$ =10V, $R_{G}$ =9.1 $\Omega$		7	14	ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>			18	35	ns
Fall-Time	t <sub>F</sub>			3	6	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	Is				12	Α
Drain-Source Diode Forward Voltage	$V_{SD}$	1 -124 \/ -0\/			1.2	V
(Note 1)		I <sub>S</sub> =12A, V <sub>GS</sub> =0V			1.2	V

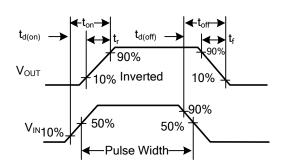
Note: 1. Pulse Test: Pulse width  $\leq$  300 $\mu$ s, Duty cycle  $\leq$  2%

<sup>2.</sup> Guaranteed by design, not subject to production testing.

### **■ TEST CIRCUITS AND WAVEFORMS**



Switching Test Circuit



Switching Waveforms

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